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TRANSMITTAL	
FORM	

(to be used for all correspondence after initial filing)

Total Number of Pages in This	Submission	Attorney Docket Number	0756-2358			
ENCLOSURES (check all that apply)						
Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s) Extension of Time Reques Express Abandonment Re Information Disclosure Sta Certified Copy of Priority Document(s) Response to Missing Parts Incomplete Application Response to Missing F under 37 CFR 1.52 or	Ass (for Dra Dec Atto Lice Peti Prov quest tement Cha Add Ten Rec I CD, Remarks	ignment Papers an Application) wing(s) laration and Power of rney insing-related Papers tion tion to Convert to a visional Application ver of Attorney, Revocation inge of Correspondence ress minal Disclaimer uest for Refund Number of CD(s) The Commissioner is	After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosures 1. Change of Correspondence Address Form 2. 3. 4. 5. 6.			
-	SIGNATURE OF AI	PPLICANT, ATTORNEY, O	DR AGENT			
Firm or Individual name Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165						
Signature	5		•			
Date	September 23, 20	02				
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In re Patent Application of

Shunpei YAMAZAKI

) Group Art Unit: 2813

Serial No. 09/939,767 <

) Examiner: D. Hogans

Filed: August 28, 2001

For: SEMICONDUCTOR DEVICE AND)

METHOD OF FABRICATING

SAME

AMENDMENT AND RESPONSE TO ELECTION REQUIREMENT

Honorable Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the Office Action of July 22, 2002, please amend the subject application as follows:

IN THE CLAIMS:

Cancel claims 8-12 without prejudice to Applicant's right to file a divisional application with respect thereto.

Please add new claims 13-34 as follows:

--13. An electronic apparatus having an electroluminescence display comprising:

a semiconductor film domprising crystalline silicon over a substrate, said semiconductor film comprising at least a channel region, and source and drain regions and containing an element for promoting crystallization of silicon; and

a gate electrode adjacent to said semiconductor film with a gate insulating film interposed therebetween, said gate electrode comprising at least one of tantalum and titanium.

wherein a concentration of said element in said source and drain regions is higher than that in other regions in said semiconductor film. 10/02/2002 SDENBOB1 00000040 09939767

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